# Dual Channel OptoHiT™ Series, High-Temperature Phototransistor Optocoupler in Small Outline 8-Pin Package

## FOD8802 Series

### **Description**

The FOD8802 dual channel optocoupler is a best-in-class phototransistor, optocoupler utilizing ON Semiconductor leading-edge proprietary process technology to achieve high operating temperature performance, up to 125°C. It consists of two aluminum gallium arsenide (AlGaAs) infrared light emitting diode optically coupled to two phototransistors, in a small outline, 8-pin SOIC package. It delivers consistent current transfer ratio at very low input current over temperature. The AlGaAs light ouput degradation performance is significantly better than the commodity optocoupler products that uses the standard GaAs, extending lifetime and reducing the guardband requirements to compensate for temperature drift. The input-output isolation voltage, Viso, is rated at 2500 VAC<sub>RMS</sub>.

#### **Features**

- Excellent CTR Linearity at High Temperature
- CTR at Very Low Input Current, IF
- High Isolation Voltage Regulated by Safety Agency, UL1577, 2500 VAC<sub>RMS</sub> for 1 min.
- Applicable to Infrared Ray Reflow, 260°C
- These are Pb-Free Devices

#### **Typical Applications**

- Primarily Suited for DC-DC Converters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control



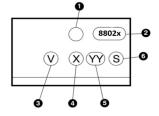
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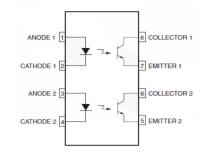
SOIC8 M SUFFIX CASE 751DZ

#### **MARKING DIAGRAM**



- 1. ON = Corporate Name
- 8802x = Device Number
- 3. V = DIN EN/IEC60747-5-5 Option
- 4. X = One-Digit Year Code
- 5. YY = Digit Work Week
- S = Assembly Package Code

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

## **Table 1. SAFETY AND INSULATION RATINGS**

As per DIN\_EN/IEC60747-5-5. this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1,	< 150 V <sub>RMS</sub>	I–IV
For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–III
Climatic Classification	40/125/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
VPR	Input–to–Output Test Voltage, Method A, $V_{IORM}$ x 1.6 = $V_{PR}$ , Type and Sample Test with $t_m$ = 10 s, Partial Discharge < 5 pC	904	Vpeak
	Input–to–Output Test Voltage, Method B, $V_{IORM}$ x 1.875 = $V_{PR}$ , 100% Production Test with $t_m$ = 1 s, Partial Discharge < 5 pC	1060	Vpeak
VIORM	Maximum Working Insulation Voltage	565	Vpeak
VIOTM	Highest Allowable Over-Voltage	4,000	Vpeak
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T <sub>S</sub>	Case Temperature (Note 1)	150	°C
IS,INPUT	Input Current (Note 1)	200	mA
Ps,output	Output Power (Note 1)	300	mW
Rio	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V (Note 1)	> 10 <sup>9</sup>	Ω

<sup>1.</sup> Safety limit values – maximum values allowed in the event of a failure.

Table 2. ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Value	Units
T <sub>STG</sub>	Storage Temperature	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature	-40 to +125	°C
T <sub>J</sub>	Junction Temperature	-50 to +150	°C
T <sub>SOL</sub>	Lead Solder Temperature (Refer to Reflow Temperature Profile)	260 for 10 sec	°C

#### **EMITTER**

I <sub>F(average)</sub>	Continuous Forward Current	20	mA
V <sub>R</sub>	Reverse Input Voltage	6	V
PD <sub>LED</sub>	Power Dissipation (Note 2)	40	mW

#### **DETECTOR**

I <sub>C(average)</sub>	Continuous Collector Current	30	mA
V <sub>CEO</sub>	Collector-Emitter Voltage	75	V
V <sub>ECO</sub>	Emitter-Collector Voltage	7	V
$PD_{C}$	Collector Power Dissipation (Note 2)	150	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Table 3. ELECTRICAL CHARACTERISTICS**

Apply over all recommended conditions ( $T_A = -40^{\circ}C$  to  $+125^{\circ}C$  unless otherwise specified). All typical values are measured at  $T_A = 25^{\circ}C$ .

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 1 mA	1.0	1.35	1.8	V
$\Delta V_F^{\prime} \Delta T_A$	Forward Voltage Coefficient	I <sub>F</sub> = 1 mA		-1.6		mV/°C
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 6 V			10	μΑ
C <sub>T</sub>	Terminal Capacitance	V = 0 V, f = 1 MHz		30		pF
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 0.5 mA, I <sub>F</sub> = 0 mA	75	130		V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	$I_E = 100 \mu A, I_F = 0 \text{ mA}$	7	12		V
I <sub>CEO</sub>	Collector Dark Current	$V_{CE} = 75 \text{ V}, I_F = 0 \text{ mA}, T_A = 25^{\circ}\text{C}$			100	nA
		V <sub>CE</sub> = 50 V, I <sub>F</sub> = 0 mA			50	μΑ
		V <sub>CE</sub> = 5 V, I <sub>F</sub> = 0 mA			30	μΑ
C <sub>CE</sub>	Capacitance	V <sub>CE</sub> = 0 V, f = 1 MHz		8		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>2.</sup> Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

## **Table 4. TRANSFER CHARACTERISTICS**

Apply over all recommended conditions ( $T_A = -40^{\circ}C$  to  $+125^{\circ}C$  unless otherwise specified).  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Units
			$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V } @ T_A = 25^{\circ}\text{C}$	80	120	160	
		FORMONA	I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 5 V	35	120	230	
		FOD8802A	I <sub>F</sub> = 1.6 mA, V <sub>CE</sub> = 5 V	40	125		
			I <sub>F</sub> = 3.0 mA, V <sub>CE</sub> = 5 V	45	138		
			I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 5 V @ T <sub>A</sub> = 25°C	130	195	260	
		FODGGOOD	I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 5 V	65	195	360	
		FOD8802B	I <sub>F</sub> = 1.6 mA, V <sub>CE</sub> = 5 V	70	202		
OTD	Current Transfer Ratio		I <sub>F</sub> = 3.0 mA, V <sub>CE</sub> = 5 V	75	215		0/
CTR <sub>CE</sub>	(collector-emiiter)		$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V } @ T_A = 25^{\circ}\text{C}$	200	300	400	%
		FOD8802C	$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	100	300	560	
		FUD6602C	$I_F = 1.6 \text{ mA}, V_{CE} = 5 \text{ V}$	110	312		
			$I_F = 3.0 \text{ mA}, V_{CE} = 5 \text{ V}$	115	330		
			$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V } @ T_A = 25^{\circ}\text{C}$	100		400	
		FOD8802D	$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	45		560	
		FOD6602D	$I_F = 1.6 \text{ mA}, V_{CE} = 5 \text{ V}$	50			
			$I_F = 3.0 \text{ mA}, V_{CE} = 5 \text{ V}$	55			
			$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V } @ T_A = 25^{\circ}\text{C}$	65	108	150	
		EOD8803A	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	30	108		
		FOD8802A	I <sub>F</sub> = 1.6 mA, V <sub>CE</sub> = 0.4 V	25	104		- %
			I <sub>F</sub> = 3.0 mA, V <sub>CE</sub> = 0.4 V	20	92		
			$I_F$ = 1.0 mA, $V_{CE}$ = 0.4 V @ $T_A$ = 25°C	90	168	245	
			$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	45	168		
			$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	40	155		
CTD	Saturated Current Transfer Ratio		$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	35	132		
CTR <sub>CE(SAT)</sub>	(collector-emiiter)		$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V } @ T_A = 25^{\circ}\text{C}$	140	238	380	70
	,	,	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	75	238		-
		FOD8802C	$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	65	215		
			$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	55	177		
			$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V } @ T_A = 25^{\circ}\text{C}$	70		380	
		FOD8802D	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	35			
		1 0000020	$I_F = 1.6 \text{ mA}, V_{CE} = 0.4 \text{ V}$	30			
			$I_F = 3.0 \text{ mA}, V_{CE} = 0.4 \text{ V}$	25			
			I <sub>F</sub> = 1.0 mA, I <sub>C</sub> = 0.3 mA		0.17	0.40	]
		FOD8802A	$I_F = 1.6 \text{ mA}, I_C = 0.4 \text{ mA}$		0.16	0.40	
			$I_F = 3.0 \text{ mA}, I_C = 0.6 \text{ mA}$		0.15	0.40	
			$I_F = 1.0 \text{ mA}, I_C = 0.45 \text{ mA}$		0.17	0.40	]
		FOD8802B	$I_F = 1.6 \text{ mA}, I_C = 0.6 \text{ mA}$		0.16	0.40	]
V <sub>0</sub> =:=:=	Saturation voltage		I <sub>F</sub> = 3.0 mA, I <sub>C</sub> = 1.0 mA		0.16	0.40	]
V <sub>CE(SAT)</sub>	Gaturation voltage		I <sub>F</sub> = 1.0 mA, I <sub>C</sub> = 0.75 mA		0.18	0.40	V
		FOD8802C	I <sub>F</sub> = 1.6 mA, I <sub>C</sub> = 1.0 mA		0.17	0.40	
			I <sub>F</sub> = 3.0 mA, I <sub>C</sub> = 1.6 mA		0.17	0.40	]
			I <sub>F</sub> = 1.0 mA, I <sub>C</sub> = 0.45 mA			0.40	]
		FOD8802D	I <sub>F</sub> = 1.6 mA, I <sub>C</sub> = 0.60 mA			0.40	]
			I <sub>F</sub> = 3.0 mA, I <sub>C</sub> = 1.00 mA			0.40	

## **Table 5. SWITCHING CHARACTERISTICS**

Apply over all recommended conditions ( $T_A = -40^{\circ}C$  to  $+125^{\circ}C$  unless otherwise specified). All typical values are measured at  $T_A = 25^{\circ}C$ .

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
	Turn On Time	$I_F$ = 1.6 mA, $V_{CC}$ = 5 V, $R_L$ = 0.75 k $\Omega$	1	6	20	μs
t <sub>ON</sub>	Turri on Time	$I_F$ = 1.6 mA, $V_{CC}$ = 5 V, $R_L$ = 4.7 k $\Omega$		6		μs
	Turn Off Time	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 0.75 \text{ k}\Omega$	1	6	20	μs
t <sub>OFF</sub>	Turn Oil Time	$I_F$ = 1.6 mA, $V_{CC}$ = 5 V, $R_L$ = 4.7 k $\Omega$		40		μs
t <sub>R</sub>	Output Rise Time (10% -90%)	$I_F$ = 1.6 mA, $V_{CC}$ = 5 V, $R_L$ = 0.75 k $\Omega$		6		μs
t <sub>F</sub>	Output Fall Time (90% -10%)	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 0.75 \text{ k}\Omega$		7		μs
CM <sub>H</sub>	Common Mode Rejection Voltage (Transient Immunity Output High)	$I_F$ = 0 mA, $V_{CC}$ = 5 V, $R_L$ = 4.7k $\Omega$ VCM = 500 V (Note 3)		10		kV/μs
CML	Common Mode Rejection Voltage (Transient Immunity Output Low)	$I_F = 1.6 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 4.7 \text{ k}\Omega$ $V\text{CM} = 500 \text{ V} \text{ (Note 3)}$		10		kV/μs

<sup>3.</sup> Common mode transient immunity at output high is the maximum tolerable positive dVcm/dt on the leading edge of the common mode impulse signal, Vcm, to assure that the output will remain high.

#### **Table 6. ISOLATION CHARACTERISTICS**

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	Freq = 60 Hz, t = 1.0 min, $I_{I-O} \le$ 10 $\mu$ A (Notes 4, 5)	2,500			VAC <sub>RMS</sub>
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 V (Note 4)	10 <sup>11</sup>			Ω
C <sub>ISO</sub>	Isolation Capacitance	Frequency = 1 MHz		0.6		pF

<sup>4.</sup> Device is considered a two terminal device: Pins 1 and 2 are shorted together and Pins 3 and 4 are shorted together.

<sup>5. 2,500</sup> VAC<sub>RMS</sub> for 1 minute duration is equivalent to 3,000 VAC<sub>RMS</sub> for 1 second duration.

## **TEST CIRCUIT**

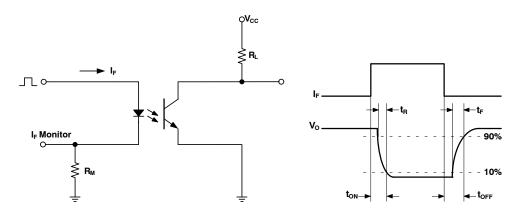


Figure 1. Switching Test Circuit and Waveform

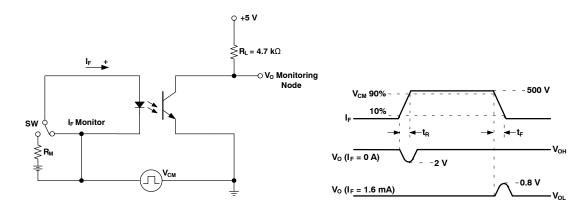


Figure 2. Test Circuit for Instantaneous Common-Mode Rejection Voltage

#### TYPICAL PERFORMANCE CHARACTERISTICS

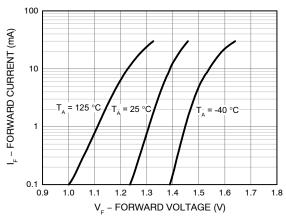


Figure 3. Forward Current vs. Forward Voltage

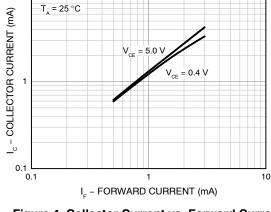


Figure 4. Collector Current vs. Forward Current

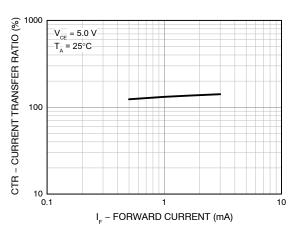


Figure 5. Current Transfer Ratio vs. Forward Current

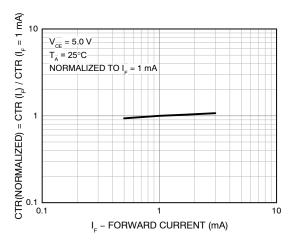


Figure 6. Normalized CTR vs. Forward Current

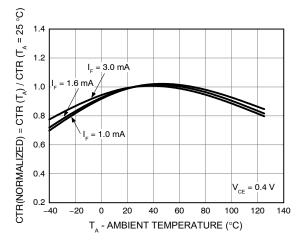


Figure 7. Normalized CTR vs. Ambient Temperature

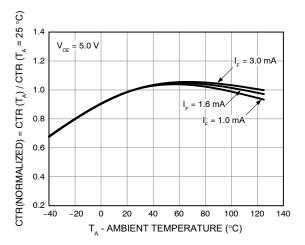


Figure 8. Normalized CTR vs. Ambient Temperature

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

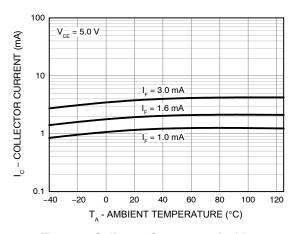


Figure 9. Collector Current vs. Ambient Temperature

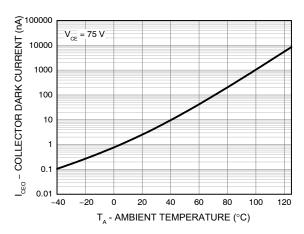


Figure 11. Collector Dark Current vs. Ambient Temperature

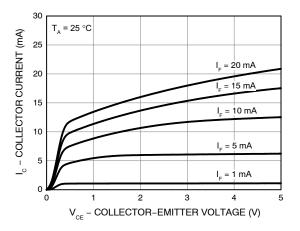


Figure 13. Collector Current vs. Collector-Emitter Voltage

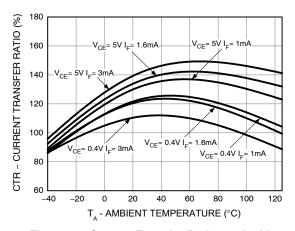


Figure 10. Current Transfer Ratio vs. Ambient Temperature

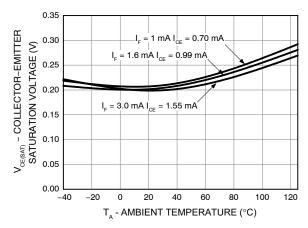


Figure 12. Collector–Emitter Saturation Voltage vs. Ambient Temperature

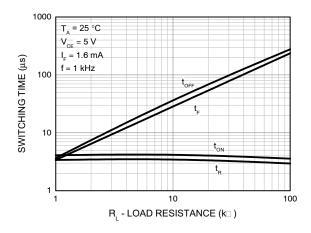


Figure 14. Switching Time vs. Load Resistance

#### **REFLOW PROFILE**

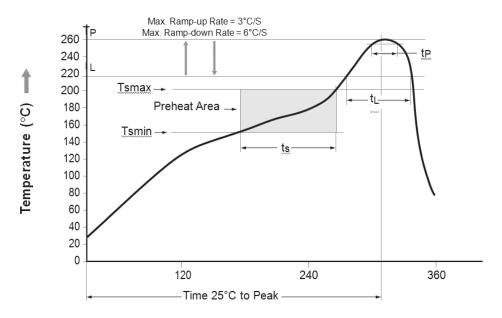


Figure 15. Reflow Profile

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

## **ORDERING INFORMATION** (Note 6)

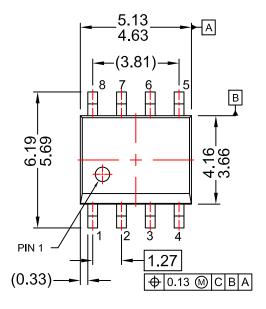
Part Number	Package	Packing Method
FOD8802A	Small Outline 8-Pin	Tube (100 units per tube)
FOD8802AR2	Small Outline 8-Pin	Tape and Reel (2,500 units per reel)
FOD8802AV	Small Outline 8-Pin DIN EN/IEC60747-5-5 Option (pending approval)	Tube (100 units per tube)
FOD8802AR2V	Small Outline 8-Pin DIN EN/ IEC60747-5-5 Option (pending approval)	Tape and Reel (2,500 units per reel)

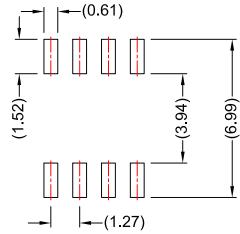
<sup>6.</sup> The product orderable part number system listed in this table also applies to the FOD8802A, FOD8802B, FOD8802C and FOD8802D products.

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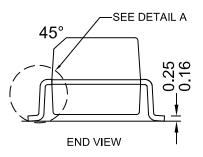
**DATE 30 SEP 2016** 





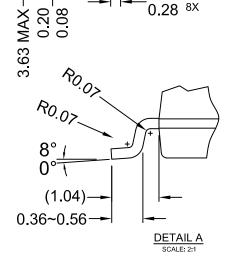
С O.10 C 0.53 0.28 8X







- A) NO STANDARD APPLIES TO THIS PACKAGE
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M.



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